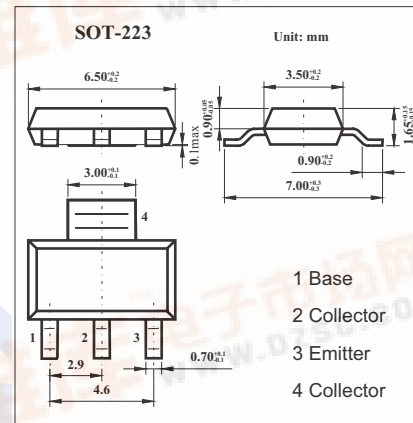


SMD Type Transistors

2.0W Surface Mount Complementary PNP Silicon Power Transistor KZT2955 (CZT2955)

Features

- High current (max. 6A).
- Low voltage (max. 60V).



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-100	V
Collector - emitter vottage	V <sub>CER</sub>	-70	V
Collector-emitter voltage	V <sub>CEO</sub>	-60	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Collector current	I <sub>C</sub>	-6	A
Base current	I <sub>B</sub>	-3	A
Power dissipation	P <sub>D</sub>	2	W
Thermal resistance,Junctiion-to-ambient	R <sub>θJA</sub>	62.5	°C/W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> =-30mA	-60			V
Collector to emitter breakdown voltage	V <sub>CER</sub>	I <sub>C</sub> =-30mA,R <sub>BE</sub> =100Ω	-70			V
Collctor cutoff current	I <sub>CEO</sub>	V <sub>CE</sub> =-30V			-700	μA
	I <sub>CEV</sub>	V <sub>CE</sub> =-100V,V <sub>EB</sub> =-1.5V			1.0	mA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = -7.0 V			-5.0	m A
DC current gain	h <sub>FE</sub>	I <sub>C</sub> = - 4.0A; V <sub>CE</sub> = -4.0 V	20		70	
		I <sub>C</sub> = -6.0A; V <sub>CE</sub> = -4.0V	5.0			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -4.0A; I <sub>B</sub> = - 400mA			-1.1	V
Base to emitter ON voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> =-4.0V,I <sub>C</sub> =-4.0A			-1.5	V
Transition frequency	f <sub>T</sub>	I <sub>C</sub> =- 500mA; V <sub>CE</sub> =-10V; f = 1.0 MHz	2.5			MHz

